

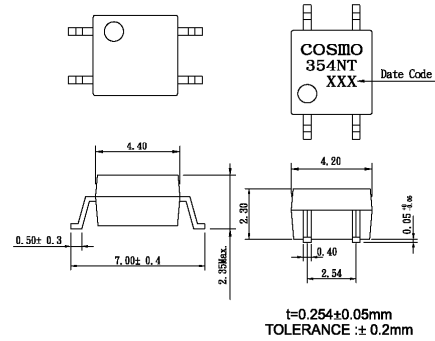
Features

1. Ac inputs.
2. Opaque type, mini-flat package.
3. Subminiature type (The volume is smaller than that of our conventional DIP type by as far as 30%)
4. Isolation voltage between input and output (Viso:3750Vrms).

Applications

1. Hybrid substrates that require high density mounting.
2. Programmable controllers.

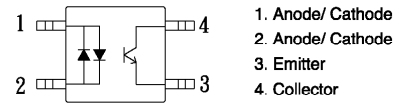
Outside Dimension : Unit (mm)



Classification table of current transfer ratio is shown below.

RANK MARK	CTR(%)
A	50 TO 150
B	20 TO 400

Schematic : Top View



Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Input	Forward current	IF	± 50 mA
	Peak forward current	IFM	± 1 A
	Power dissipation	P	70 mW
Output	Collector-emitter voltage	VCEO	60 V
	Emitter-collector voltage	VECO	5 V
	Collector current	IC	50 mA
	Collector power dissipation	Pc	150 mW
	Total power dissipation	Ptot	170 mW
Isolation voltage 1 minute	Viso	3750	Vrms
Operating temperature	Topr	-30 to +100	°C
Storage temperature	Tstg	-40 to +125	°C
Soldering temperature 10 second	Tsol	260	°C

Electro-optical Characteristics

(Ta=25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	IF = ± 20mA	—	1.2	1.4	V
	Terminal capacitance	V = 0, f = 1kHz	—	30	250	pF
Output	Collector dark current	VCE = 20V, IF = 0	—	—	0.1	uA
	Collector-emitter breakdown voltage	IC = 0.1mA, IF = 0	60	—	—	V
	Emitter-collector breakdown voltage	IE = 100uA, IF = 0	5	—	—	V
Transfer characteristics	Current transfer ratio	IF = ± 1mA, VCE = 5V	20	—	400	%
	Collector-emitter saturation voltage	IF = ± 20mA, IC = 1mA	—	0.1	0.3	V
	Isolation resistance	DC500V, 40 to 80%RH	5X10 ¹⁰	10 ¹¹	—	ohm
	Floating capacitance	V = 0, f = 1MHz	—	0.6	1.0	pF
	Response time (Rise)	VCE = 2V, IC = 2mA, RL = 100ohm	—	4	18	us
	Response time (Fall)		—	3	18	us

